

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claims 1-19. (Cancelled)

20. (New) A semiconductor integrated circuit device comprising:
- a semiconductor substrate of a first conductive type;
 - a first well of a second conductive type provided in the semiconductor substrate;
 - a second well of the first conductive type provided in the first well;
 - a third well of the second conductive type provided in the semiconductor substrate;
 - a fourth well of the first conductive type provided in the third well;
 - semiconductor elements provided in the first and second wells, the semiconductor elements constructing a first functional integrated circuit;
 - semiconductor elements provided in the third and fourth wells, the semiconductor elements constructing a second functional integrated circuit;
 - a first internal power source voltage generating circuit provided in the first well, the first internal power source voltage generating circuit configured to generate a first internal power source voltage being applied to the first functional integrated circuit; and
 - a second internal power source voltage generating circuit provided in the third well, the second internal power source voltage generating circuit configured to generate a second internal power source voltage being applied to the second functional integrated circuit.

21. (New) The device according to claim 20, wherein each of the first and second functional integrated circuits has a dedicated output terminal for outputting an outputting an output signal when a potential is applied to the potential application terminal thereof.

22. (New) The device according to claim 20, further comprising:
a first controlling circuit provided in the first well and configured to control the first internal power source voltage generating circuit based on an inputted first control signal; and
a second controlling circuit provided in the third well and configured to control the second internal power source voltage generating circuit based on an inputted second control signal.

23. (New) The device according to claim 20, wherein the first internal power source voltage generating circuit generates the first internal power source voltage according to an external power source voltage, and the second internal power source voltage generating circuit generates the second internal power source voltage according to the first internal power source voltage.

24. (New) The device according to claim 23, further comprising:
a first controlling circuit provided in the first well and configured to control the first internal power source voltage generating circuit which turned-on and turned-off generating the first internal power source voltage based on an inputted first control signal; and
a second controlling circuit provided in the third well and configured to control the second internal power source voltage generating circuit which turned-on and turned-off generating the second internal power source voltage based on an inputted second control signal.

25. (New) The device according to claim 20, wherein the first functional integrated circuit and the second functional integrated circuit each include at least one of a non-volatile memory circuit, an analog circuit, a digital circuit, a digital/analog conversion circuit, a static random access memory circuit and a dynamic random access memory circuit.

26. (New) The device according to claim 20, further comprising:
a fifth well of the second conductive type provided in the first well;
a sixth well of the second conductive type provided in the third well,
wherein the first functional integrated circuit comprises semiconductor elements provided in the fifth well, and the second functional integrated circuit comprises semiconductor elements provided in the sixth well.

27. (New) The device according to claim 26, wherein each of the first and second functional integrated circuits has a dedicated output terminal for outputting an outputting an output signal when a potential is applied to the potential application terminal thereof.

28. (New) The device according to claim 26, further comprising:
a first controlling circuit provided in the first well and configured to control the first internal power source voltage generating circuit based on an inputted first control signal; and
a second controlling circuit provided in the third well and configured to control the second internal power source voltage generating circuit based on an inputted second control signal.

29. (New) The device according to claim 26, wherein the first internal power source voltage generating circuit generates the first internal power source voltage according to an external power source voltage, and the second internal

power source voltage generating circuit generates the second internal power source voltage according to the first internal power source voltage.

30. New) The device according to claim 29, further comprising:

a first controlling circuit provided in the first well and configured to control the first internal power source voltage generating circuit which turned-on and turned-off generating the first internal power source voltage based on an inputted first control signal; and

a second controlling circuit provided in the third well and configured to control the second internal power source voltage generating circuit which turned-on and turned-off generating the second internal power source voltage based on an inputted second control signal.

31. New) The device according to claim 26, wherein the first functional integrated circuit and the second functional integrated circuit each include at least one of a non-volatile memory circuit, an analog circuit, a digital circuit, a digital/analog conversion circuit, a static random access memory circuit and a dynamic random access memory circuit.

32. (New) A semiconductor integrated circuit device comprising:

a semiconductor substrate of a first conductive type;

a first well of a second conductive type provided in the semiconductor substrate;

a second well of the first conductive type provided in the first well;

a third well of the second conductive type provided in the semiconductor substrate;

a fourth well of the first conductive type provided in the third well;

semiconductor elements provided in the first and second wells, the semiconductor elements constructing a first functional integrated circuit;

semiconductor elements provided in the third and fourth wells, the semiconductor elements constructing a second functional integrated circuit; and

an internal power source voltage generating circuit provided in the first well, the internal power source voltage generating circuit configured to generate a first internal power source voltage being applied to the first functional integrated circuit and a second internal power source voltage being applied to the second functional integrated circuit.

33. (New) The device according to claim 32, wherein each of the first and second functional integrated circuits has a dedicated output terminal for outputting an outputting an output signal when a potential is applied to the potential application terminal thereof.

34. (New) The device according to claim 32, wherein the internal power source voltage generating circuit generates the first and second internal power source voltages according to an external power source voltage.

35. (New) The device according to claim 34, further comprising:

a controlling circuit provided in the first well and configured to control the internal power source voltage generating circuit which turned-on and turned-off generating the first internal power source voltage based on an inputted first control signal, and configured to control the second internal power source voltage generating circuit which turned-on and turned-off generating the second internal power source voltage based on an inputted second control signal.

36. (New) The device according to claim 32, further comprising:

a fifth well of the second conductive type provided in the first well;
a sixth well of the second conductive type provided in the third well,
wherein the first functional integrated circuit comprises semiconductor elements
provided in the fifth well, and the second functional integrated circuit comprises
semiconductor elements provided in the sixth well.

37. (New) The device according to claim 36, wherein each of the first and
second functional integrated circuits has a dedicated output terminal for outputting
an outputting an output signal when a potential is applied to the potential
application terminal thereof.

38. (New) The device according to claim 36, wherein the internal power
source voltage generating circuit generates the first and second internal power
source voltages according to an external power source voltage.

39. (New) The device according to claim 38, further comprising:
a controlling circuit provided in the first well and configured to control
the internal power source voltage generating circuit which turned-on and turned-off
generating the first internal power source voltage based on an inputted first control
signal, and configured to control the second internal power source voltage
generating circuit which turned-on and turned-off generating the second internal
power source voltage based on an inputted second control signal.